



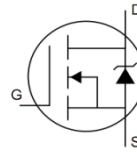
3

The ZM2305T combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON) . This device is ideal for load switch and battery protection applications.

2

high cell density Trench technology
 DS(ON) to minimize conductive loss

Product Summary



nd Synchronous Rectifier

Part NO.	ZM2305T
Marking	2305
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

T_c =25

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	V
Continuous Drain Current	I _{D@TC=25}	-5.8	A
	I _{D@TC=75}	-4.4	A
	I _{D@TC=100}	-3.7	A
Pulsed Drain Current	I _{DM}	-12	A
Total Power Dissipation	P _D	10	W
Total Power Dissipation(TA=25)	P _{D@TA=25}	0.7	W
Operating Junction Temperature	T _J	-55 to 150	
Storage Temperature	T _{STG}	-55 to 150	
Single Pulse Avalanche Energy	E _{AS}	45	mJ

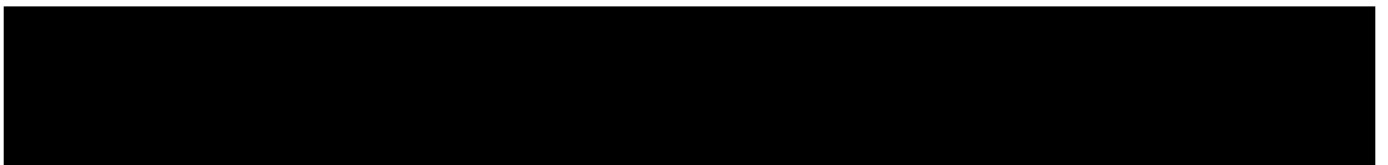




Fig.7 Switching Time Measurement Circuit

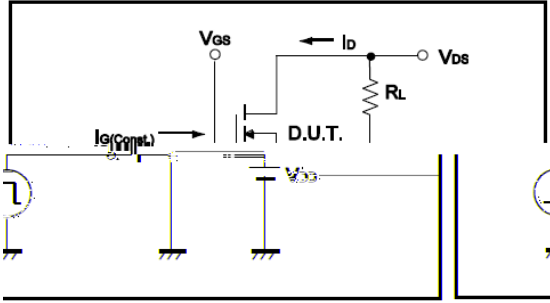


Fig.8 Gate Charge Waveform

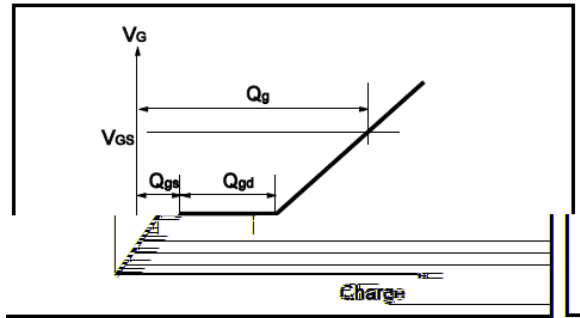


Fig.9 Switching Time Measurement Circuit

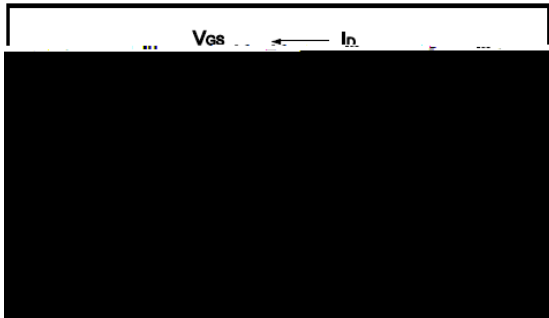


Fig.10 Gate Charge Waveform

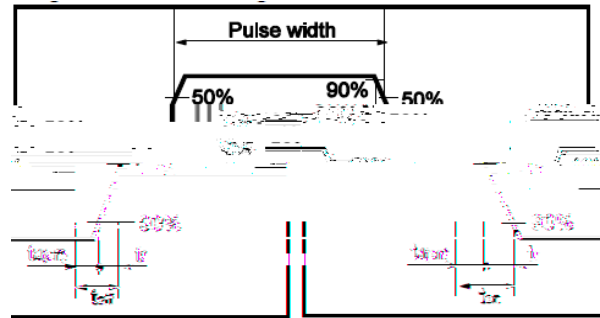


Fig.11 Avalanche Measurement Circuit

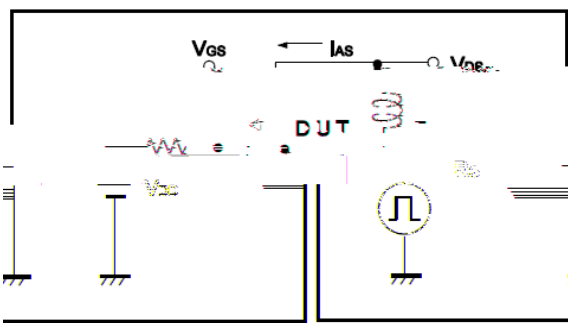
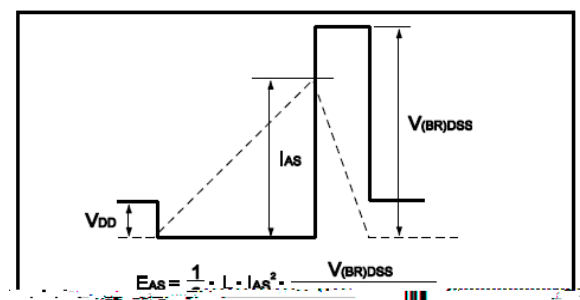


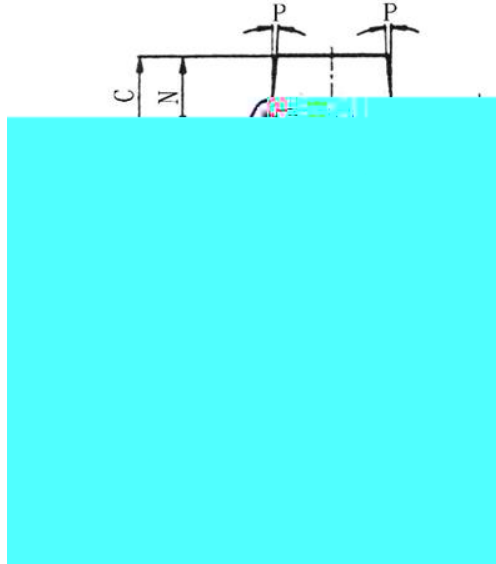
Fig.12 Avalanche Waveform





(SOT23)

Unit mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20
K	0.00		0.10
L	0.45	0.55	0.65
M	0.20		
N	0.90	1.00	1.20
P		7°	